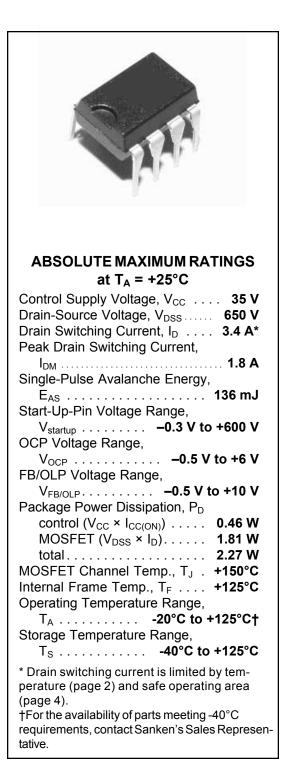


STR-A6153E



Universal-Input/20 W Flyback Switching Regulator

The STR-A6153E is a PRC topology (fixed off-time) regulator specifically designed to satisfy the requirements for increased integration and reliability in flyback converters. It incorporates a primary control and drive circuit with avalanche-rated power MOSFET. The STR-A6153E features high switching current and avalanche-energy ratings and low on-resistance.

Covering the power range from below 24 watts for a 230 VAC input, or 20 watts for a universal (85 to 264 VAC) input, this device can be used in a range of applications, from DVD and VCR players to ac adapters for cellular phones and digital cameras. An auto-standby function reduces power consumption at light load, while multiple protections, including the avalanche-energy guaranteed MOSFET, provide high reliability of system design.

Cycle-by-cycle current limiting, undervoltage lockout with hysteresis, overvoltage protection, and thermal shutdown protect the power supply during the normal overload and fault conditions. Overvoltage protection and thermal shutdown are latched after a short delay. The latch may be reset by cycling the input supply. Low start-up current and a low-power standby mode selected from the secondary circuit completes a comprehensive suite of features. The STR-A6153E is provided in an 8-pin mini-DIP plastic package.

FEATURES AND BENEFITS

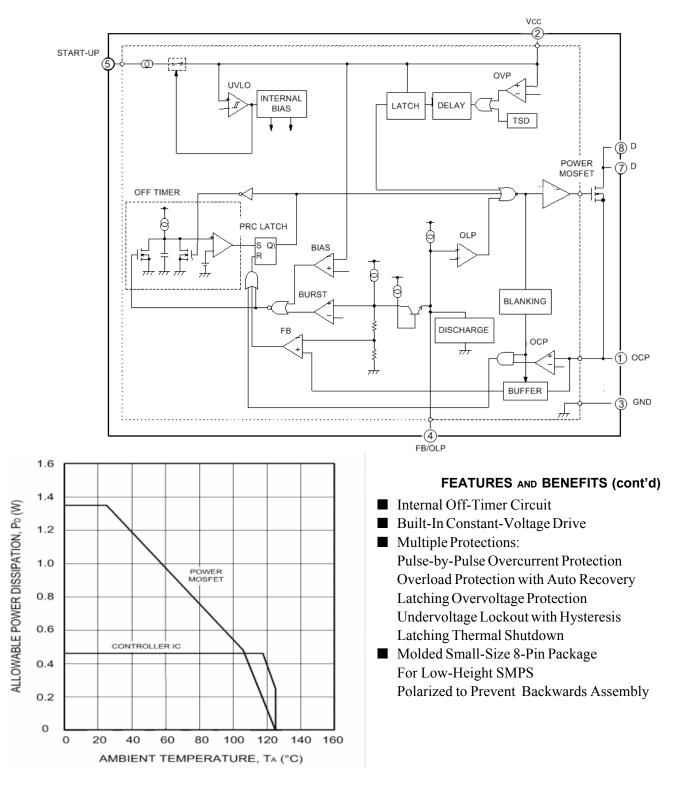
- Rugged 650 V Avalanche-Rated MOSFET Simplified Surge Absorption No V_{DSS} Derating Required
- $\blacksquare 1.9 \Omega \mathbf{r}_{\mathrm{DS(on)}}$
- Two Operational Modes by Automatic Switching: PRC Mode for Normal Operation Burst Mode for Stand-By Operation or Light Loads
- Built-In Leading Edge Blanking
- Low Start-Up Current Start-Up Circuit Disabled in Operation
- Low Operating Current (1.5 mA typ)
- Automatic Burst Stand-By (intermittent operation) Input Power <0.1 W at No Load</p>

-continued

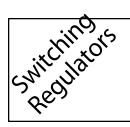
Always order by complete part number, e.g., STR-A6153E







FUNCTIONAL BLOCK DIAGRAM



ELECTRICAL CHARACTERISTICS at $T_A = 25^{\circ}$ C, $V_{CC} = 20$ V (unless otherwise specified).

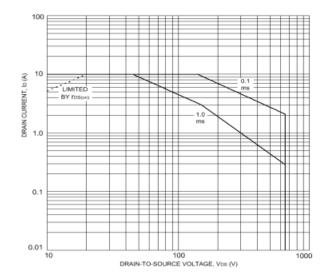
	Pin			Ratings			
Characteristic	No.	Symbol	Test Conditions	Min	Тур	Мах	Units
Drain-to-Source Breakdown Volt.	8 - 1	V _{(BR)DSS}	I _D = 300 μA,	650	-	-	V
		()	$V_1 - V_3 = 0 V$ (short)				
Drain Leakage Current	8 - 1	I _{DSS}	V _{DS} = 650 V,	-	-	300	μA
			$V_1 - V_3 = 0 V$ (short)				
On-State Resistance	8 - 1	r _{DS(on)}	I _D = 0.4 A	-	-	1.9	Ω
MOSFET Switching Time	8 - 3	t _f	-	-	-	250	ns
Operation Start Voltage	2 - 3	V _{CC(ON)}	V _{CC} = 0 → 19.2 V	16	17.5	19.2	V
Operation Stop Voltage	2 - 3	V _{CC(OFF)}	V _{CC} = 19.2 → 9 V	9.0	10	11	V
Circuit Current in Operation	2 - 3	I _{CC(ON)}	-	-	-	4.0	mA
Circuit Current in Non-Operation	2 - 3	I _{CC(OFF)}	V _{CC} = 14 V	-	-	50	μA
Maximum OFF Time	8 - 3	t _{OFF}	-	10.5	11.5	12.5	μs
OCP Threshold Voltage	1 - 3	V _{OCP}	-	0.96	1.13	1.28	V
Leading Edge Blanking Time	8 - 3	t _b	-	200	320	480	ns
Burst Threshold Voltage	4 - 3	V _{burst}		0.66	0.75	0.84	V
OLP Threshold Voltage	4 - 3	V _{OLP}	-	6.5	7.2	7.9	V
Current at OLP Operation	4 - 3	I _{OLP}	-	-18.2	-26	-34.1	μA
Maximum FB Current	4 - 3	I _{FB(MAX)}	-	220	300	390	μA
Start-Up Current	5 - 3	I _{startup}	V _{CC} = 15 V	340	790	1230	μA
Start-Up Circuit Leakage Current	5 - 3	I _{start(leak)}	-	-	-	30	μA
OVP Operation Voltage	2 - 3	V _{CC(OVP)}	V _{CC} = 0 → 34.1 V	28.7	31.2	34.1	V
OVP/TSD Latch Sustaining Current	2 - 3	I _{CC(H)}	V _{CC} =34.1 → 8.5 V	-	-	200	μA
OVP/TSD Latch Release Voltage	2 - 3	V _{cc}	V _{CC} =34.1 → 6.6 V	6.6	7.3	8.0	V
Thermal Shutdown	-	Tj	-	110	-	-	°C
Thermal Resistance	-	$R_{_{ hetaJF}}$	-	-	-	52	°C/W

WARNING — These devices are designed to be operated at lethal voltages and energy levels. Circuit designs that embody these components must conform with applicable safety requirements. Precautions must be taken to prevent accidental contact with power-line potentials. Do not connect grounded test equipment.

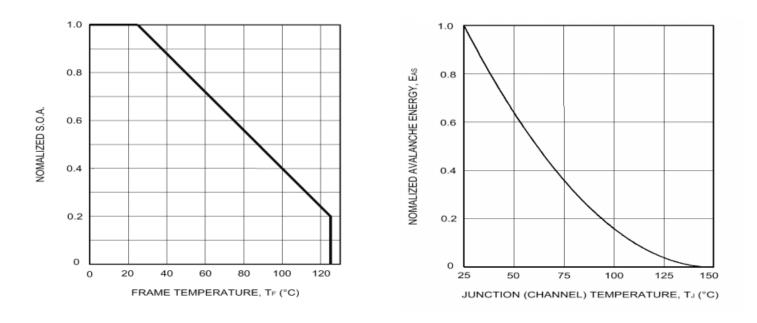
The use of an isolation transformer is recommended during circuit development and breadboarding.

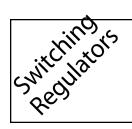




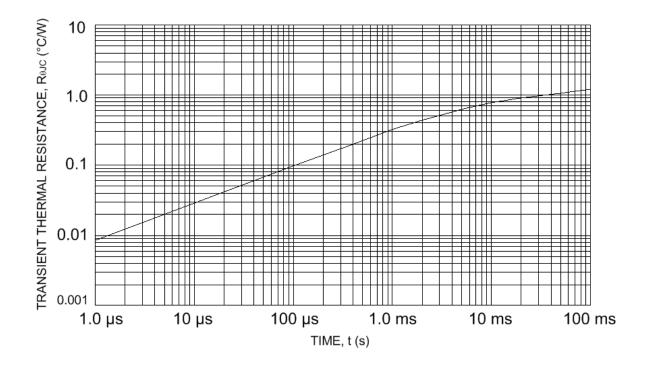


Avalanche energy is measured at V_{DD} = 99 V, L = 20 mH, I_L = 3.4 A.

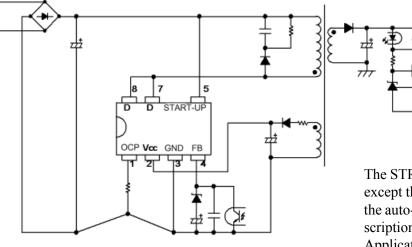




MOSFET TYPICAL CHARACTERISTICS (cont'd)

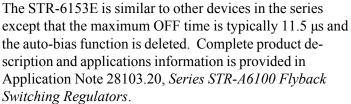






APPLICATIONS INFORMATION

Typical Application



- The contents in this document are subject to changes, for improvement and other purposes, without notice. Make sure that this is the latest revision of the document before use.
- Application and operation examples described in this document are quoted for the sole purpose of reference for the use of the products herein and Sanken can assume no responsibility for any infringement of industrial property rights, intellectual property rights or any other rights of Sanken or any third party which may result from its use.
- Although Sanken undertakes to enhance the quality and reliability of its products, the occurrence of failure and defect of semiconductor products at a certain rate is inevitable. Users of Sanken products are requested to take, at their own risk, preventative measures including safety design of the equipment or systems against any possible injury, death, fires or damages to the society due to device failure or malfunction.
- Sanken products listed in this document are designed and intended for the use as components in general purpose electronic equipment or apparatus (home appliances, office equipment, telecommunication equipment, measuring equipment, etc.).

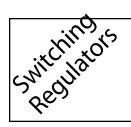
When considering the use of Sanken products in the applications where higher reliability is required (transportation equipment and its control systems, traffic signal control systems or equipment, fire/crime alarm systems, various safety devices, etc.), and whenever long life expectancy is required even in general purpose electronic equipment or apparatus, please contact your nearest Sanken sales representative to discuss, prior to the use of the products herein.

The use of Sanken products without the written consent of Sanken in the applications where extremely high reliability is required (aerospace equipment, nuclear power control systems, life support systems, etc.) is strictly prohibited.

• In the case that you use Sanken products or design your products by using Sanken products, the reliability largely depends on the degree of derating to be made to the rated values. Derating may be interpreted as a case that an operation range is set by derating the load from each rated value or surge voltage or noise is considered for derating in order to assure or improve the reliability. In general, derating factors include electric stresses such as electric voltage, electric current, electric power etc., environmental stresses such as ambient temperature, humidity etc. and thermal stress caused due to self-heating of semiconductor products. For these stresses, instantaneous values, maximum values and minimum values must be taken into consideration.

In addition, it should be noted that since power devices or IC's including power devices have large self-heating value, the degree of derating of junction temperature affects the reliability significantly.

- When using the products specified herein by either (i) combining other products or materials therewith or (ii) physically, chemically or otherwise processing or treating the products, please duly consider all possible risks that may result from all such uses in advance and proceed therewith at your own responsibility.
- Anti radioactive ray design is not considered for the products listed herein.
- Sanken assumes no responsibility for any troubles, such as dropping products caused during transportation out of Sanken's distribution network.
- The contents in this document must not be transcribed or copied without Sanken's written consent.



PACKAGE DIMENSIONS

